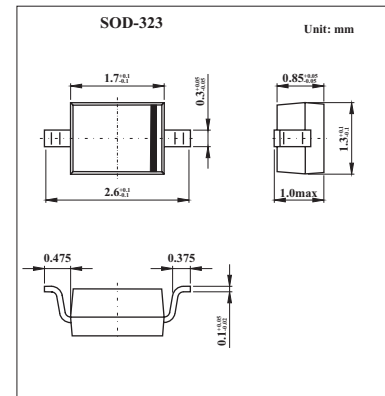


## Silicon Epitaxial Planar Diode

## 1SV276

## ■ Features

- High Capacitance Ratio:  $C_{1V}/C_{4V} = 2.0$  (Typ.)
- Low Series Resistance:  $r_s = 0.22 \Omega$  (Typ.)

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Value	Unit
Reverse Voltage	$V_R$	10	V
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to +125	$^\circ\text{C}$

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Reverse Voltage	$V_R$	$I_R = 1 \mu\text{A}$	10			V
Reverse Current	$I_R$	$V_R = 10 \text{V}$			3	nA
Capacitance	$C_{1V}$	$f = 1 \text{MHz}; V_R = 1 \text{V}$	15	16	17	pF
	$C_{4V}$	$f = 1 \text{MHz}; V_R = 4 \text{V}$	7	8	8.5	
Capacitance Ratio	$C_{1V}/C_{4V}$		1.8	2.0		
Series Resistance	$r_s$	$V_R = 1 \text{V}, f = 470 \text{MHz}$		0.22	0.4	$\Omega$

## ■ Marking

Marking	TL
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